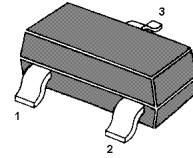


## MMBT5400 PNP Silicon Epitaxial Planar Transistor

for high voltage .

Marking Code:2L



1.Base 2.Emitter 3.Collector  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	130	V
Collector Emitter Voltage	$-V_{CEO}$	120	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current Continuous	$-I_C$	600	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-55 to +150	$^\circ\text{C}$

### Characteristics at $T_{amb}=25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}=5\text{V}$ , $-I_C=10\text{mA}$	$h_{FE}$	40	180	-
Collector Base Breakdown Voltage at $-I_C=0.1\text{mA}$	$-V_{(BR)CBO}$	130	-	V
Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	120	-	V
Emitter Base Breakdown Voltage at $-I_E=0.1\text{mA}$	$-V_{(BR)EBO}$	5	-	V
Collector Cutoff Current at $-V_{CB}=100\text{V}$	$-I_{CBO}$	-	0.05	$\mu\text{A}$
Emitter Cutoff Current at $-V_{EB}=3\text{V}$	$-I_{EBO}$	-	0.05	$\mu\text{A}$
Collector Emitter Saturation Voltage at $-I_C=50\text{mA}$ , $-I_B=5\text{mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C=50\text{mA}$ , $-I_B=5\text{mA}$	$-V_{BE(sat)}$	-	1	V
Current Gain Bandwidth Product at $-V_{CE}=10\text{V}$ , $-I_C=10\text{mA}$	$f_T$	100	-	MHz
Output Capacitance at $-V_{CB}=10\text{V}$ , $f=1\text{MHz}$	$C_{ob}$	-	6	pF
Noise Figure at $-I_C=0.2\text{mA}$ , $-V_{CE}=5\text{V}$ , $f=15.7\text{KHz}$	NF	-	8	dB

## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

